Update on IV measurement in HVCOMS CHESSI chip

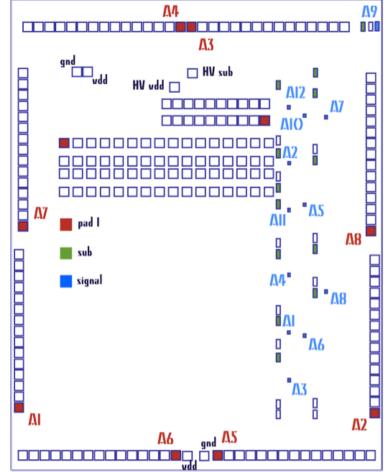
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Introduction

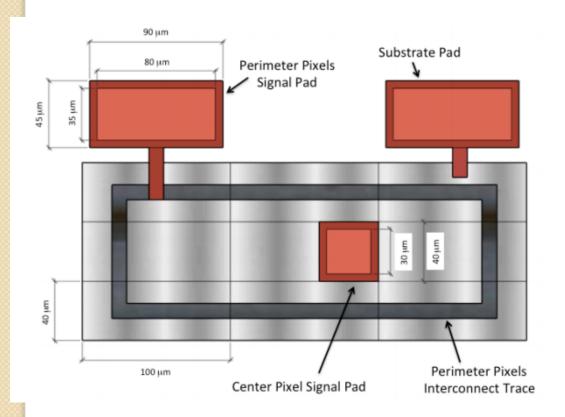
- AMS CHESSI HV-CMOS chip is available for testing
- Preliminary I-V and capacitance results :
 - I-V measurement
 - C-V Measurement

PPA#	Pixel width	Pixel length	Diode Area Fraction	Metal opening ratio	Extra circuitry
PPA01	45µm	100µm	30%	13.0%	
PPA02	45µm	100µm	50.4%	34.5%	
PPA03	45µm	200µm	30%	22.7%	
PPA04	45µm	200µm	50.4%	44.0%	
PPA05	45µm	400µm	30%	27.4%	
PPA06	45µm	400µm	50.4%	48.7%	
PPA07	45µm	800µm	30%	29.8%	
PPA08	45µm	800µm	50.4%	51.0%	
PPA09	45µm	100µm	30%	13.0%	Special bond pads for E-TCT
PPA10	45µm	200µm	30%	22.7%	Without contact ring around each pixel, but with contact ring around the entire array having a separate pad
PPA11	45µm	200μm	30%	22.7%	With contact ring around each pixel that violates the design rules by having a symmetric width. NOTE this pixel was added twice
PPA12	45µm	200µm	30%	22.7%	With contact ring around each pixel that violates the design rules by having a symmetric width. NOTE this pixel was added twice



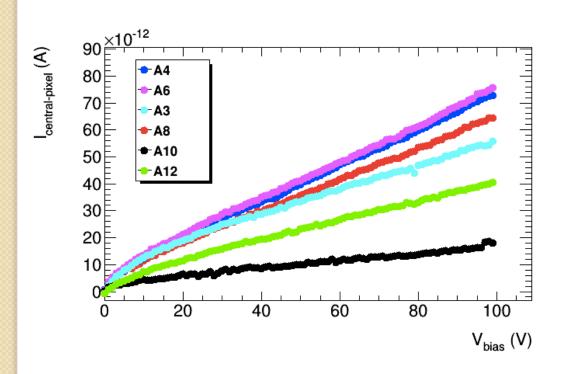
pixel IV measurement setup

- Substrate: grounded
- Perimeter pixels: +HV
- Central pixel: +HV



Old I-V results in Dec Ist

- Leakage current is up to 90pA
- Found very large noise contribution
- About ~50pA noise when it is open
 - Mainly due to BNC cable



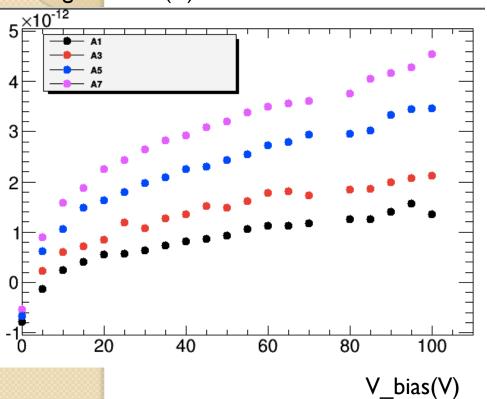
Low noise setup

- In order to measure low leakage current.
- We now used low loss SMI cable.
 - Noise level about 500 fA



Updated results on central pixel I-V

Leakage current(A)



PPA#	Pixel width	Pixel length	Diode Area Fraction	Metal opening ratio
PPA01	45µm	100µm	30%	13.0%
PPA03	45µm	200μm	30%	22.7%
PPA05	45μm	400µm	30%	27.4%
PPA07	45µm	800µm	30%	29.8%

Summary

- Updated results from I-V measurements.
 - Reduce noise using low noise setup.
 - I-V curve makes more sense now.
 - leakage currents scale with pixel size.